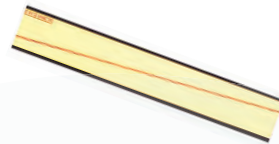


High Power SOA Chip



Part Number: CHP-2900

High Power SOA Chip
Single-Mode SOA Fabry-Perot
Wavelength at 1310nm O-band



Features

- High Output Power
- High Dynamic Range
- High Efficiency
- Standard SOA Bare Die
- Cost Effective

Application

- OTDR
- LiDAR
- Free Space Communications
- Network Test Equipment



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

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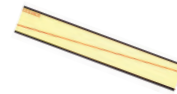
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High Power SOA Chip



Specification

CHP-2900



Optical	Symbol	Typ. CHP-2900	Units
Center Wavelength	λ_c	1310	nm
Output Power @1A*	P_{out}	0.45	watts ($\pm 10\%$)
Aperture Width	AW	4	μm
Aperture Height	AH	1	μm
Gain @ Pin = 10 μ W	G	35	dB
Gain Bandwidth	BW	80	nm
Beam Exit Angle	θ_{EXT}	19.5	Degree
Noise Figure	NF	6	dB
Polarization Extinction Ratio	PER	18	dB
Fast Axis Div.	$\theta_{\perp}$	28	Deg FWHM
Slow Axis Div.	$\theta_{\parallel}$	16	Deg FWHM
Front Facet Reflectivity		<0.1%	
Rear Face Reflectivity		<0.1%	
Waveguide		Tilted Straight	
Electrical	Symbol		Units
Operating Current	I_{op}	1	A
Operating Voltage	V_{op}	2	V
Mechanical		Range	Units
Chip Length		2500	μm
Chip Width		500	μm
Operating Temp.**		-20 to 75	$^{\circ}C$
Storage Temp.		-40 to 85	$^{\circ}C$

*Optical Power for 1310nm COC-288 and COC-290 with SOA drive current @ 1A and estimated Pin @ 7mW

*Optical Power for 1550nm COC-285 and COC-287 with SOA drive current @ 1A and estimated Pin @ 21mW

* Optical output power depends on the seed laser power, coupling efficiency, and thermal management.

*Specified values are rated at a constant heat sink temperature of 20 $^{\circ}C$.

**High temperature operation will reduce performance and MTTF.
Unless otherwise indicated all values are nominal.

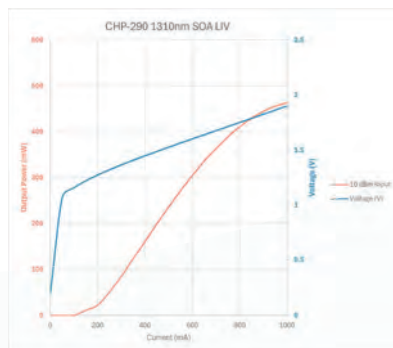
High Power SOA Chip



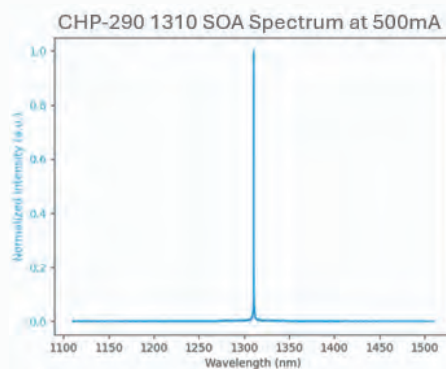
SemiNex SOA CHP-2900

Graphs & Data

Typical CHP L-I-V Characteristics



Typical CHP Output Spectrum



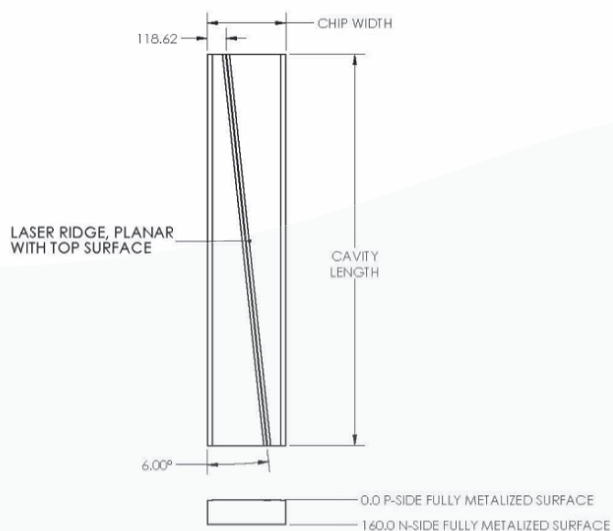
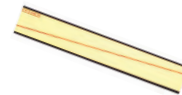
*Graphs and Data were collected from mounted parts

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High Power SOA Chip



Mechanical Drawing



CHIP ATTRIBUTES	
WAVELENGTH	1310nm ±20nm
APERTURE WIDTH	4μm ±1μm
CHIP WIDTH	0.500mm ±10μm
THICKNESS	1.60μm ±10μm
CAVITY LENGTH	2.5mm ±10μm

P-METAL		
MATERIAL	THICKNESS (nm)	TOLERANCE (nm)
Ti	50	±10
Pt	125	±25
Au	250	±50

N-METAL		
MATERIAL	THICKNESS (nm)	TOLERANCE (nm)
Ti	30	±10
Pt	125	±25
Au	400	±40

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